

Transistor(NPN)

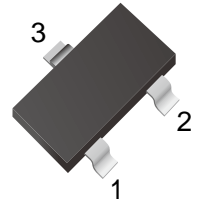
Features

- Complementary to LT856/LT857/LT858
- Power Dissipation of 200mW
- Ideally suited for automatic insertion
- For switching and AF amplifier applications

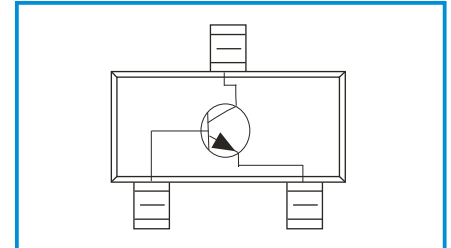
Mechanical Data

- Small Outline Plastic Package
- Epoxy UL: 94V-0
- Mounting Position: Any

1. BASE
2. EMITTER
3. COLLECTOR



Functional Diagram



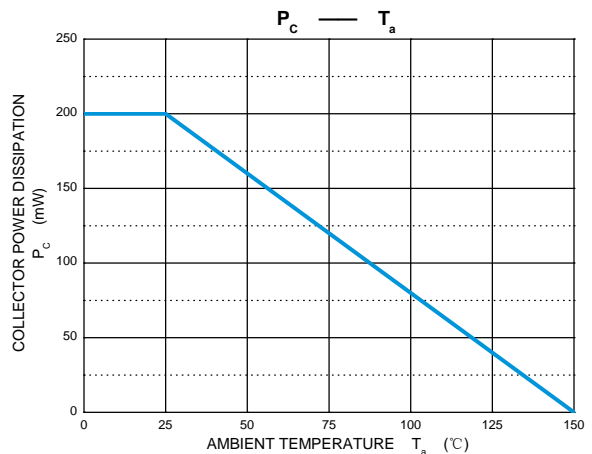
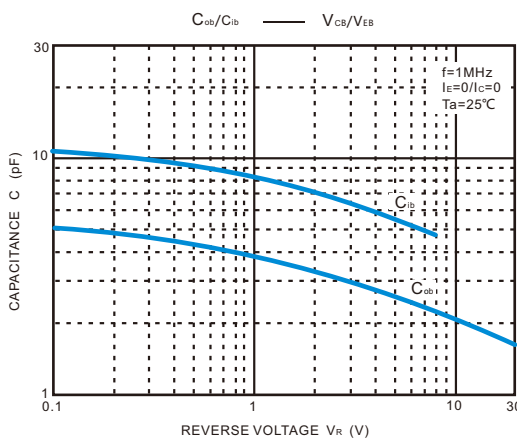
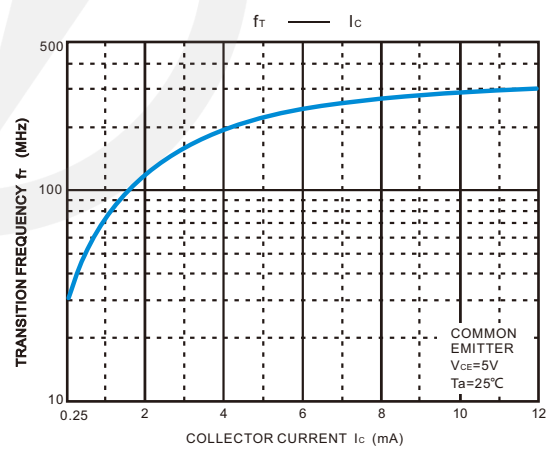
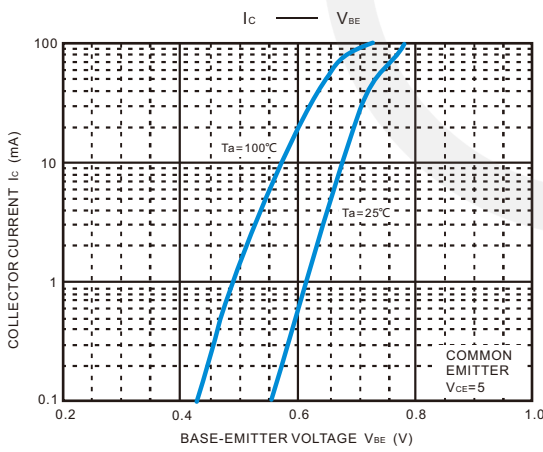
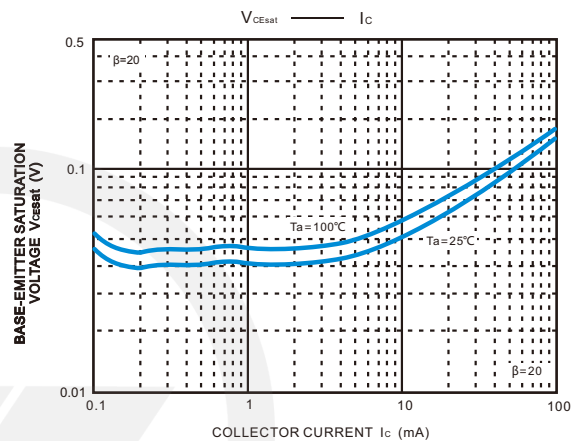
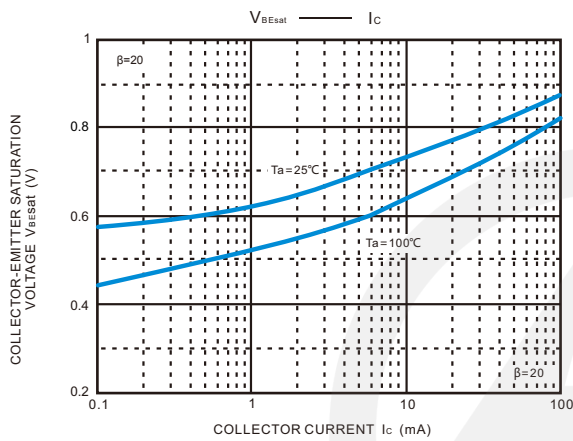
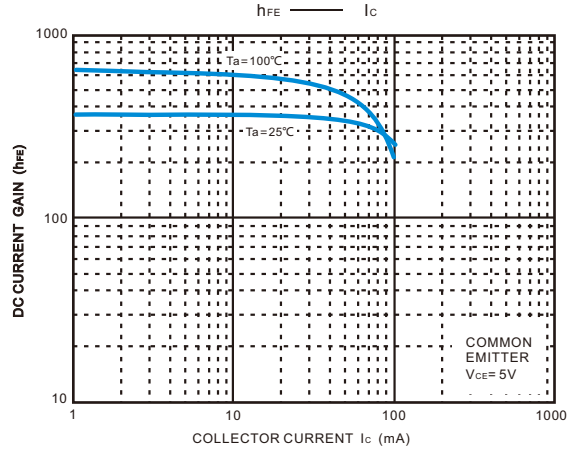
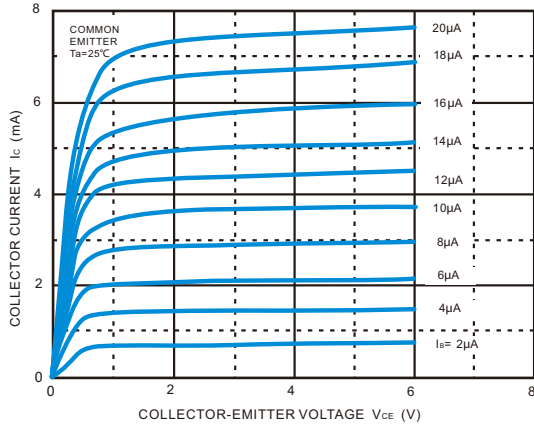
Maximum Ratings (Ta=25 unless otherwise noted)

Parameters	Symbol		Value	Unit
Collector-Base Voltage	V _{CB0}	LT846	80	V
		LT847	50	
		LT848	30	
Collector-Emitter Voltage	V _{CEO}	LT846	65	V
		LT847	45	
		LT848	30	
Emitter -Base Voltage	V _{EBO}		6	V
Collector Current-Continuous	I _C		100	mA
Collector Power Dissipation	P _C		200	mW
Junction Temperature	T _j		150	°C
Storage Temperature	T _{stg}		-55-+150	°C
Thermal resistance From junction to ambient	R _{θJA}		625	°C/W

Electrical characteristics (Ta=25 unless otherwise specified)

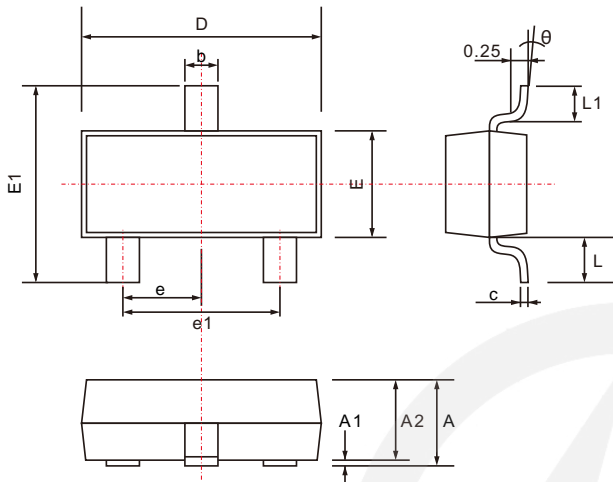
Parameter	Symbols	Test Condition	Limits		Unit	
			Min	Max		
Collector-base breakdown voltage	V _{(BR)CBO}	IC=10uA, IE=0	LT846	80	V	
			LT847	50		
			LT848	30		
Collector-emitter breakdown voltage	V _{(BR)CEO}	IC=10mA, IB=0	LT846	65	V	
			LT847	45		
			LT848	30		
Emitter-base breakdown voltage	V _{(BR)EBO}	IE=10uA, IC=0		6	V	
Collector cut-off current	I _{CBO}	V _{CB} =70V, IE=0	LT846	100	nA	
		V _{CB} =50V, IE=0	LT847			
		V _{CB} =30V, IE=0	LT848			
Collector cut-off current	I _{CEO}	V _{CE} =60V, IB=0	LT846	100	nA	
		V _{CE} =45V, IB=0	LT847			
		V _{CE} =30V, IB=0	LT848			
Emitter cut-off current	I _{EBO}	VEB=5V, IC=0		100	nA	
DC current gain	h _{FE}	V _{CE} =5V, IC=2mA	LT846A;LT847A;LT848A	110	220	
			LT846B;LT847B;LT848B	200	450	
			LT847C;LT848C	420	800	
Collector-emitter saturation voltage	V _{CE(sat)}	IC=100mA, IB=5mA		0.50	V	
Base -emitter saturation voltage	V _{BE(sat)}	IC=100mA, IB=5mA		1.10	V	
Transition frequency	f _T	V _{CE} =5V, IC=10mA,f=100MHz		100	MHz	
Collector output capacitance	C _{ob}	V _{CB} =10V, f=1MHz		4.5	pF	

Typical Characteristics



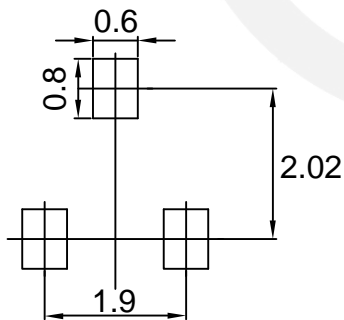
SOT-23 Package Outline

Unit: mm



SYMBOL	DIMENSIONS	
	MIN.	MAX.
A	0.900	1.200
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.200
D	2.700	3.100
E	1.200	1.400
E1	2.200	3.000
e	0.950 TYP.	
e1	1.750	2.050
L	0.550 TYP.	
L1	0.300	0.500
θ	0°	8°

SOT-23 Suggested Pad Layout

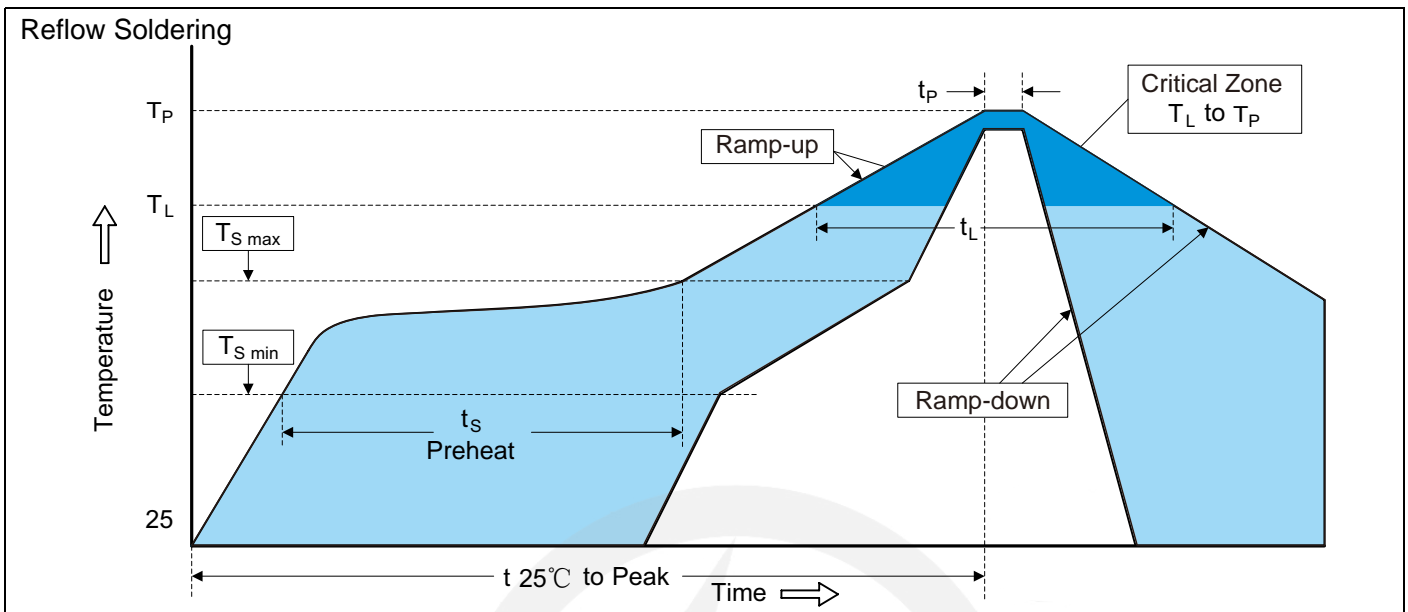


Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$
3. The pad layout is for reference purpose only.

Marking

LT846A=1A	LT846B=1B	
LT847A=1E	LT847B=1F	LT847C=1G
LT848A=1J	LT848B=1K	LT848C=1L

Recommended Soldering Conditions

Recommended Conditions

Profile Feature	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	3°C/second max.
Preheat -Temperature Min ($T_{S\ min}$) -Temperature Max ($T_{S\ max}$) -Time (min to max) (t_s)	150°C 200°C 60-180 seconds
$T_{S\ max}$ to T_L -Ramp-up Rate	3°C/second max.
Time maintained above: -Temperature (T_L) -Time (t_L)	217°C 60-150 seconds
Peak Temperature (T_P)	260°C
Time within 5°C of actual Peak Temperature (t_P)	20-40 seconds
Ramp-down Rate	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

7" Reel


D2	$\Phi 178.0 \pm 2.0$
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D3	$\Phi 50.0 \text{ Min.}$
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D4	$\Phi 13.0 \pm 0.5$
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W1	16.0 ± 2.0
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Quantity: 3000PCS